Shinji Yokogawa

List of Publications by Year
in descending order

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66	533	11	19
papers	citations	h-index	g-index

840776 794594

72	72	72	197
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Analysis of the Trends Between Indoor Carbon Dioxide Concentration and Plug-Level Electricity Usage Through Topological Data Analysis. IEEE Sensors Journal, 2022, 22, 1424-1434.	4.7	2
2	Controlling Power Supply Paths in VG Hub Networks Using a Hybrid Type Control Algorithm. Ambient Intelligence and Smart Environments, 2022, , .	0.3	1
3	Distributed Power-Delivery Decision for a USB-PD-based Network. , 2022, , .		1
4	Trends boetween indoor CO2 concentration and electricity usage through topological data analysis. , 2021, , .		1
5	Compact model for estimating area-level photovoltaic power generation on facade surface using 3D city model and solar radiation simulation. , 2021, , .		1
6	Seven View Points and Reliability Engineering Scheme for Preventing Reliability Problems. International Journal of Reliability, Quality and Safety Engineering, 2020, 27, 2050006.	0.6	1
7	Applications of lifetime distribution functions with two shape parameters for reliability analysis in advanced interconnect technologies: a brief review. Japanese Journal of Applied Physics, 2020, 59, SL0802.	1.5	2
8	Humidity reliability of commercial flash memories for long-term storage. Japanese Journal of Applied Physics, 2020, 59, SLLC01.	1.5	2
9	Bayesian inference of a lifetime distribution parameter on the time-dependent dielectric breakdown with clustering defects. Japanese Journal of Applied Physics, 2019, 58, SHHG02.	1.5	2
10	A Simple Prediction Method for Chip-Level Electromigration Lifetime Using Generalized Gamma Distribution. , 2019, , .		2
11	Liner- and barrier-free NiAl metallization: A perspective from TDDB reliability and interface status. Applied Surface Science, 2019, 497, 143810.	6.1	13
12	Lifetime prediction model of Cu-based metallization against moisture under temperature and humidity accelerations. Japanese Journal of Applied Physics, 2019, 58, SBBC01.	1.5	4
13	An Approach to Renewable-Energy Dominant Grids via Distributed Electrical Energy Platform for IoT Systems. , 2019, , .		5
14	Overlapped Grouping Optimization for Wind-Photovoltaic-Battery Hybrid System by Graph Enumeration. IEEJ Transactions on Electronics, Information and Systems, 2019, 139, 786-795.	0.2	0
15	Survey of critical failure events in on-chip interconnect by fault tree analysis. Japanese Journal of Applied Physics, 2018, 57, 07MG01.	1.5	2
16	Statistical evaluation method for lifetime distribution in field-accelerated time-dependent dielectric breakdown using two-step probability plot and multilink test scheme. Japanese Journal of Applied Physics, 2018, 57, 07MG02.	1.5	2
17	Oxidation Structure Change of Copper Surface Depending on Accelerated Humidity. , 2018, , .		1
18	Reliability evaluation of defect accounted time-dependent dielectric breakdown with competing-mixture distribution. , 2018, , .		2

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19	On the Overlapping Decentralized Operation for Wind-Photovoltaic-Battery Hybrid System. IEEJ Transactions on Electronics, Information and Systems, 2018, 138, 1554-1565.	0.2	0
20	Impacts of censoring on lifetime analysis by two-step probability plot in defect clustered TDDB. , 2017, , .		3
21	Two-step probability plot for parameter estimation of lifetime distribution affected by defect clustering in time-dependent dielectric breakdown. Japanese Journal of Applied Physics, 2017, 56, 07KG02.	1.5	4
22	Advanced Metallization for ULSI Applications. Japanese Journal of Applied Physics, 2017, 56, 07K001.	1.5	0
23	Simulation study for lifetime distribution of middle-of-line time-dependent dielectric breakdown affected by global and local spacing variations. Japanese Journal of Applied Physics, 2016, 55, 06JF02.	1.5	9
24	Virtual grid for renewable energy society. , 2015, , .		2
25	Statistical characteristics of lifetime distribution based on defect clustering for time-dependent dielectric breakdown in middle- and back-end-of-line. Japanese Journal of Applied Physics, 2015, 54, 05EC02.	1.5	11
26	Lifetime prediction model of stress-induced voiding in Cu/low-Îº interconnects. Japanese Journal of Applied Physics, 2014, 53, 05GA03.	1.5	3
27	Lifetime prediction for stress-induced voiding in nose-shape lines by using a stress-diffusion analytical model. , 2014, , .		1
28	Highly reliable molecular-pore-stacking (MPS)/Cu interconnects featuring best combination of post-etching treatment and resputtering processes. Microelectronic Engineering, 2014, 118, 72-78.	2.4	3
29	Reliability and Interface in Cu Interconnects: Contribution and Control of Interface for EM, SIV, and TDDB. Hyomen Kagaku, 2014, 35, 256-261.	0.0	0
30	Highly reliable enhanced nitride interface process of barrier low-k using ultra-thin SiN with moisture blocking capability. Microelectronic Engineering, 2013, 112, 97-102.	2.4	3
31	Lifetime Distribution Analysis of Stress-Induced Voiding Based on Void Nucleation and Growth in Cu/Low-$kappa$ Interconnects. IEEE Transactions on Device and Materials Reliability, 2013, 13, 272-276.	2.0	11
32	Moisture absorption impact on Cu alloy/low-k reliability during process queue time. Microelectronic Engineering, 2013, 106, 205-209.	2.4	8
33	Thermal Transient Response and Its Modeling for Joule Heating in Cu/Low-$kappa$ Interconnects Under Pulsed Current. Japanese Journal of Applied Physics, 2012, 51, 05EC06.	1.5	3
34	Thermal Transient Response and Its Modeling for Joule Heating in Cu/Low-Îº Interconnects Under Pulsed Current. Japanese Journal of Applied Physics, 2012, 51, 05EC06.	1.5	0
35	Highly reliable Enhanced Nitride Interface (ENI) process of barrier Low-k using absorption-free Ultra-Thin SiN (UT-SiN). , 2011, , .		0
36	Impact of low-k moisture absorption during queue-time on Cu-alloy/low-k reliability and its suppression. , 2011, , .		1

#	ARTICLE	IF	CITATIONS
37	Failure analysis of fine Cu patterning by shaveâ€off profiling. Surface and Interface Analysis, 2011, 43, 621-624.	1.8	2
38	Role of Impurity Segregation into Cu/Cap Interface and Grain Boundary in Resistivity and Electromigration of Cu/Low-kInterconnects. Japanese Journal of Applied Physics, 2011, 50, 05EA02.	1.5	8
39	Statistics of breakdown field and time-dependent dielectric breakdown in contact-to-poly modules. , 2011, , .		21
40	Highly reliable molecular-pore-stacking (MPS)/Cu interconnects using novel post-etching treatment (PET) for 28 nm-node and beyond. , 2011, , .		0
41	Role of Impurity Segregation into Cu/Cap Interface and Grain Boundary in Resistivity and Electromigration of Cu/Low-<i>k</i>Interconnects. Japanese Journal of Applied Physics, 2011, 50, 05EA02.	1.5	4
42	Effective thermal characteristics to suppress joule heating impacts on electromigration in Cu/low-k interconnects. , 2010, , .		5
43	Statistical Analysis of Lifetime Distribution of Time-Dependent Dielectric Breakdown in Cu/Low-kInterconnects by Incorporation of Overlay Error Model. Japanese Journal of Applied Physics, 2010, 49, 05FE01.	1.5	13
44	Comparison of Lifetime Improvements in Electromigration between Ti Barrier Metal and Chemical Vapor Deposition Co Capping. Japanese Journal of Applied Physics, 2010, 49, 04DB08.	1.5	7
45	Direct observation of RTN-induced SRAM failure by accelerated testing and its application to product reliability assessment. , 2010, , .		46
46	Joule heating effects on electromigration in Cu/low-κ interconnects. , 2009, , .		7
47	Suppression of Electromigration Early Failure of Cu/Porous Low-kInterconnects Using Dummy Metal. Japanese Journal of Applied Physics, 2009, 48, 096504.	1.5	1
48	Optimization of metallization processes for 32-nm-node highly reliable ultralow-k (k=2.4)/Cu multilevel interconnects incorporating a bilayer low-k barrier cap (k=3.9). , 2009, , .		1
49	V<inf>th</inf> fluctuations due to random telegraph signal on work function control in Hf-doped silicate gate stack. Reliability Physics Symposium, 2009 IEEE International, 2009, , .	0.0	0
50	Novel scalable TDDB model for large-area MIM decoupling capacitors in high performance LSIs. , 2009, , .		0
51	Tradeoff Characteristics Between Resistivity and Reliability for Scaled-Down Cu-Based Interconnects. IEEE Transactions on Electron Devices, 2008, 55, 350-357.	3.0	24
52	Prediction of early failure due to non-visual defect on time-dependent dielectric breakdown of low-k dielectrics: Experimental verification of a yield-reliability model. , 2008, , .		9
53	Analysis of Al Doping Effects on Resistivity and Electromigration of Copper Interconnects. IEEE Transactions on Device and Materials Reliability, 2008, 8, 216-221.	2.0	35
54	Effects of Al doping on the electromigration performance of damascene Cu interconnects. Journal of Applied Physics, 2007, 101, 013513.	2.5	37

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55	Impurity Doping Effects on Electromigration Performance of Scaled-down Cu Interconnects. AIP Conference Proceedings, 2007, , .	0.4	2
56	A Robust Embedded Ladder-Oxide/Cu Multilevel Interconnect Technology for 0.13 Âµm Complementary Metal Oxide Semiconductor Generation. Japanese Journal of Applied Physics, 2007, 46, 954-961.	1.5	13
57	Analytical Study of Impurity Doping Effects on Electromigration of CU Interconnects by Employing Comprehensive Scattering Model. , 2007, , .		0
58	Electromigration lifetimes and void growth at low cumulative failure probability. Microelectronics Reliability, 2006, 46, 1415-1420.	1.7	41
59	Effects of Al Doping on Electromigration Performance of Narrow Single Damascene Cu Interconnects. , 2006, , .		4
60	Scaling Impacts on Electromigration in Narrow Single-Damascene Cu Interconnects. Japanese Journal of Applied Physics, 2005, 44, 1717-1721.	1.5	34
61	Electromigration-Induced Void Growth Kinetics in SiNx-Passivated Single-Damascene Cu Lines. Japanese Journal of Applied Physics, 2004, 43, 5990-5996.	1.5	27
62	Electromigration Performance of Multi-level Damascene Copper Interconnects. Microelectronics Reliability, 2001, 41, 1409-1416.	1.7	47
63	Full-0.56 Î¼m pitch copper interconnects for a high performance 0.15-Î¼m CMOS logic device. , 0, , .		3
64	A robust embedded ladder-oxide/Cu multilevel interconnect technology for 0.13 Î¼m CMOS generation. , 0, , .		5
65	Electromigration induced incubation, drift and threshold in single-damascene copper interconnects. , 0, , .		5
66	Stress relaxation in dual-damascene Cu interconnects to suppress stress-induced voiding. , 0, , .		13